

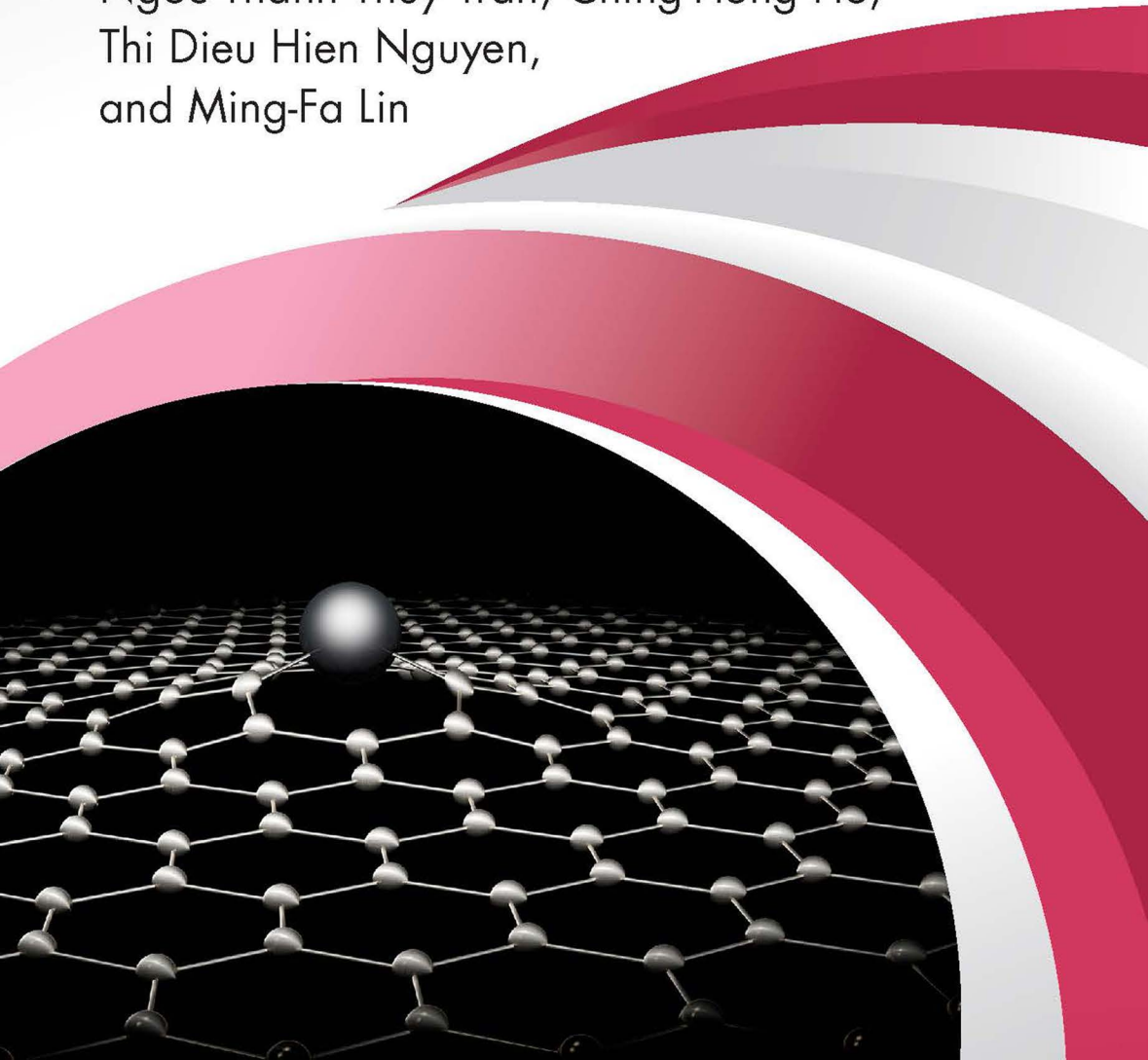


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Diverse Quasiparticle Properties of Emerging Materials

First-Principles Simulations

Edited by Tran Thi Thu Hanh, Vo Khuong Dien,
Ngoc Thanh Thuy Tran, Ching-Hong Ho,
Thi Dieu Hien Nguyen,
and Ming-Fa Lin



Diverse Quasiparticle Properties of Emerging Materials

Diverse Quasiparticle Properties of Emerging Materials: First-Principles Simulations thoroughly explores the rich and unique quasiparticle properties of emergent materials through a VASP-based theoretical framework. Evaluations and analyses are conducted on the crystal symmetries, electronic energy spectra/wave functions, spatial charge densities, van Hove singularities, magnetic moments, spin configurations, optical absorption structures with/without excitonic effects, quantum transports, and atomic coherent oscillations.

Key Features

- Illustrates various quasiparticle phenomena, mainly covering orbital hybridizations and spin-up/spin-down configurations
- Mainly focuses on electrons and holes, in which their methods and techniques could be generalized to other quasiparticles, such as phonons and photons
- Considers such emerging materials as zigzag nanotubes, nanoribbons, germanene, plumbene, bismuth chalcogenide insulators
- Includes a section on applications of these materials

This book is aimed at professionals and researchers in materials science, physics, and physical chemistry, as well as upper-level students in these fields.



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Preface

This book *Diverse Quasiparticle Properties of Emerging Materials: First-Principles Simulations* is completed with intensive cooperation in scientific research between research groups from Taiwan and Vietnam. This book comprises 20 comprehensive chapters on the theoretical framework of quasiparticle properties. There are two approaches of quasiparticle viewpoints dominating the theoretical developments, namely, first-principles simulations and phenomenological models. This work is focused on the first-principles simulations.

The calculated results include the total ground state energies/the chemical modification energies, the optimal Moiré superlattices/normal unit cells, the atom- and spin-dominated band structures/wave functions, the spatial charge/spin density distributions, the atom- orbital- and spin-decomposed van Hove singularities, the net magnetic moments, the single-particle and many-body reflectance, absorption, transmission and energy loss spectra, the ballistic electrical conductivities, the Hall quantum ones, and the vibration phonons. They are sufficient to identify the various quasiparticle behaviors and to further generalize the previous theoretical framework.

Most of the research results in this book are carried out by research groups at prestigious universities such as National Cheng Kung University, Taiwan; Ho Chi Minh City University of Technology (HCMUT)—Vietnam National University Ho Chi Minh City, Vietnam; National Kaohsiung University of Science and Technology, Taiwan; Can Tho University, Vietnam; Can Tho University of Medicine and Pharmacy, Vietnam; Thu Dau Mot University, Vietnam. We are grateful to all the authors for their excellent contributions.

This book will hopefully be of great interest to the scientific community, and it will contribute to the development of research of emergent materials.



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1 Introduction

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A lot of emergent materials, which have been/will be successfully generated by various physical and chemical methods, are outstanding candidates in exploring diverse phenomena of quasiparticle properties both theoretically and experimentally. Such unusual materials cover graphene-related systems (diamond, bulk graphites, layered graphene, carbon nanotubes, graphene nanoribbons, fullerenes, onions, and chains) [1–8], few-layer group-IV and group-V ones (silicene/germanene/tinene/plumbene/phosphorene/bismuthene/antimonene [9–15]), core anodes, electrolytes, and cathodes of lithium-ion-based batteries [e.g., the ternary lithium titanium/silicon/iron compounds [16–19]], perovskite solar cells [20], transition-/rare-earth-metal disulfide-related compounds [21, 22], and quantum topological insulators [23]. Furthermore, they are easily modulated by chemical adsorptions/substitutions [24, 25], temperatures [26], mechanical strains [27], gate voltages [electric fields] [28], uniform/non-uniform magnetic fields [29, 30], time-dependent/static Coulomb fields [31, 32], and electromagnetic waves [33]. The intrinsic and extrinsic mechanism are very sufficient for creating diversified quasiparticle behaviors. This is clearly illustrated in crystal symmetries (Moiré superlattices or not [34, 35]), electronic energy spectra and wave functions, spatial charge densities [36], van Hove singularities [37], net magnetic moments [38], and atom- and orbital-induced spin configurations [39]. Both theoretical calculations and experimental measurements are developed to examine and verify various essential properties, being attributed to the dynamic and/or static responses of the same/composite quasiparticles (e.g., electrons/polarons [40]). This book is focused on the former, which is based on first-principles simulations [41]. The critical mechanisms in determining rich and unique phenomena are thoroughly explored from consistent physical quantities, especially for the orbital hybridizations of chemical bonds and the atom- and orbital-induced magnetic configurations [42]. Most importantly, the framework of quasiparticle viewpoints could be achieved through the systematic investigations. The predicted results are compared with the measured ones in detail [43].

In general, there are two approaches of quasiparticle viewpoints in dominating the theoretical developments (all the details in Chapter 2), namely, first-principles simulations (e.g., proposed orbital hybridizations and spin configurations in Ref [43]) and the phenomenological models (e.g., the generalized tight-binding model, the modified random-phase approximation and self-energy method; [44–46]). Each strategy must have plenty of merits and drawbacks. For example, the former/the latter can/cannot successfully deal with optimal geometries, complicated band structures of

Moiré superlattices [34], spatial multi-orbital hybridizations [47], spin density distributions [48], the net magnetic and electric moments [49], complex excitonic effects [50], the low-dimensional quantum transports [51], and the collective atom vibrations (phonon spectra and polarization displacements [52]), while they are unable/able to explore the various magnetic quantization phenomena (e.g., the featured Landau levels/magneto-optical selection rules/magneto-electronic Coulomb excitations/quantum Hall effects [53–56]), the static/dynamic charge screening abilities (such as, the unusual Friedel oscillations due to charged impurities, plasma waves arising from the external ion beam, and the quasiparticle lifetimes of few-layer graphene/coaxial carbon nanotubes [57–59]). These have been clearly identified in systematic studies, as done for graphene-related emergent materials [60]. Apparently, how to promote their direct combinations would be very useful in understanding the same/composite quasiparticles and thus would achieve much progress of basic sciences. In this work, the VASP calculations are chosen for a theoretical development, being partially supported by the model discussions. The concise motivations of each book chapter are stated in the following paragraphs.

The various high-precision experiments are developed to detect the unusual physical/chemical/materials properties in emergent materials [the details are in Chapter 3], covering the delicate examinations and analyses about the geometric, electronic, magnetic, optical, Coulomb-excitation, and transport properties. The X-ray diffraction is frequently utilized to measure the crystal structures of bulk materials since the first theory and experiment by Bragg et al., such as the different Moiré super lattices in ternary lithium-titanium [61], lithium-silicon [62] and lithium-iron [63] oxide compounds (anode/electrolyte/cathode materials of lithium-ion-based batteries [64–66]), and stage- n graphite intercalation compounds (n corresponding to the number of graphitic layers between two intercalant ones; [67]). How to evaluate the reliable charge densities from the measured patterns are very interesting challenges. Specifically, the elastic scattering of the incident electron beams is available in observing the three-zero dimensional condensed-matter systems, in which both reflection low-energy electron diffraction (RLEED [68]) and tunneling electron microscopy (TEM [69]) are capable of providing the top and side views of surface-related structures, respectively. These two methods have clearly verified the low-dimensional crystal symmetries within the coaxial, few-layer, and deformed composite structures, such as single-/multi-walled carbon nanotubes [70], layered graphene systems with the different layers [71], normal stacking configurations [72] and twisted angles [73], planar/folded/curved/scrolled graphene nanoribbons [74–77], and buckled monolayer/bilayer silicene/germanene/tinene/plumbene [the significant coupling effects of stacking and buckling [78–81]]. As to the nano-scaled crystal structures, scanning tunneling microscopy (STM [82]) can reveal the periodical atom arrangements [83] and the local defects (vacancy, adatom intercalation and guest-atom substitution [84–86]). It is well known that STM is very successful in identifying the chirality and radius of a single-walled carbon nanotube [87], the edge boundary of an achiral/chiral graphene nanoribbon [88], the honeycomb lattices of monolayer group-IV systems [89], and the non-hexagonal phosphorene [90]. In addition, the spin-polarized STM is enhanced for its spatial resolution and thus is very useful in identifying the prominent ferromagnetism related to the atomic spin configurations [48].

The theoretical predictions on electronic energy spectra and wave functions are directly verified from scanning tunneling spectroscopy (STS [91]) and angle resolved photoemission spectroscopy (ARPES [92]). STS measurements can fully examine the dimension-dependent van Hove singularities due to the band-edge states. The very successful cases cover the geometry-determined symmetric peaks and the metallic or semiconducting behaviors in single-walled carbon nanotubes, the chirality- and width-dependent energy gaps of 1D graphene nanoribbons, the layer-number-, stacking-, twist-angle-, and doping-enriched band overlaps, band gaps, energy dispersion relations in few-layer graphene systems, and the greatly modified band properties across the Fermi level from 2D group-IV and group-V systems on distinct substrates [93]. Specifically, the spin-polarized STS measurements can distinguish the spin-split density of states [94]. On the ARPES side, their measurements can clearly reveal the quasiparticle energy spectra and lifetimes of occupied electronic states. The up-to-now works show that they have shown the diverse band dispersion for 2D materials, e.g., the linear, parabolic, partially flat, and oscillatory energy bands in AB- and ABC-stacked graphene systems [95]. The 1D graphene nanoribbons are observed to exhibit the parabolic bands in the presence of semiconducting behaviors [96]. In addition, no published papers are found about the ARPES spectra of 1D carbon nanotubes and 3D lithium titanium/silicon/iron oxides. The difficulty in defining vectors/transferred momenta and too many valence subbands should be the critical factors. Specifically, the wave-vector-dependent distribution width of ARPES spectra are available in determining the quasiparticle lifetimes, e.g., the enhanced Coulomb decay rates in monolayer alkali-doped graphene [97].

Four kinds of optical spectroscopies are able to measure the frequency-dependent reflectance [98], absorption [99], transmission [100], and photoluminescence spectra [101]. Specifically, the last ones are designed for the clear identifications of many-body effects (the greatly reduced threshold frequency, the extra-prominent absorption peaks of excitonic bound states, and the strongly modified features of single-particle vertical transitions [102]). Which kinds of measurements are suitable strongly depends on the sample thickness. For example, reflectance, transmission, and absorption spectra have been successfully measured for AB-stacked graphite [103], few-layered graphene systems with the different stacking configurations and carbon nanotubes, respectively. Furthermore, these examinations are able to clarify the low-energy π -electronic excitations and middle-energy σ -electronic ones [104], the layer-number- and stacking-enriched absorption structures [105], and the excitonic/Aharonov-Bohm effects [106]. It should be noted that the optical reflectance and photoluminescence spectra are detected for the multi-component lithium oxides [107], in which the measured results are too rough to achieve important conclusions. This is attributed to Moiré superlattices in creating a lot of valence and conduction subbands. However, the VASP simulations in this book will clearly specify the close relations between the active orbital hybridizations and the prominent absorption structures [108]. While the dynamic cases are recovered to the static ones [109] (the long wavelength limit is extended to any moment transfers [110]), the measured transport properties can clarify the semiconducting or metallic behaviors (the electron energy loss spectra are able to comprehend the single-particle and collective charge excitations [111]), especially for the quantum Hall conductivities of layered

material [56] (the unusual plasmon modes in low-dimensional systems [112]). Very interestingly, experimental measurements are frequently utilized to fully explore the screening abilities of quasiparticle charges [113].

Numerous 2D materials have been synthesized and predicted since the discovery of graphene [114]. As a result, many studies for the structures and properties of 2D materials are available [115–117]. Hexagons are basic building blocks of the crystal structures for most 2D materials. Following the structure–property relationships that have been commonly explored to discover new materials [118], we expect that the properties of 2D materials can be modified if the building blocks for these nanomaterials are changed from hexagons to pentagons. Very recently, significant efforts have focused on stabilization of the pentagonal structure based on carbons, that is monolayer penta-graphene [119]. Penta-graphene (PG) is extracted from bulk T12-carbon phase. This phase is obtained by heating an interlocking-hexagon-based metastable carbon phase at high temperature [120]. It is found that the monolayer PG is an indirect band-gap semiconductor with a band gap of ~ 3.25 eV [121] which is smaller than SiC [122], BN [123], and BeO [124] nanostructures. Those studies showed that this structure has obtained dynamical, thermal, and mechanical stability. In a similar way to graphene, the PG sheets can be cut along typical crystallographic orientations in order to construct various penta-graphene nanoribbons (PGNRs) to obtain quasi-one-dimensional materials. Their electronic properties were systemically investigated [125] including confinement effects and quasiparticle phenomena. The resulting four typical nanoribbons, with different edge configurations, are denoted as zigzag-zigzag penta-graphene nanoribbon (ZZ-PG NR), zigzag-armchair penta-graphene nanoribbon (ZA-PG NR), zigzag-armchair penta-graphene nanoribbon (AA-PG NR), and sawtooth-sawtooth penta-graphene nanoribbon (SS-PG NR). This study confirmed that SS-PG NR is the most stable structure when compared with the other three types of PGNRs with similar width. SS-PG NR possesses semiconductor properties. Electronic and transport properties of the sawtooth-sawtooth penta-graphene nanoribbons were systematically investigated by using the density-functional theory (DFT) in combination with the non-equilibrium Green's function (NEGF) formalism in this chapter. Quasiparticle related electronic diversity of many SS-PG NR structures is investigated in Chapter 4. This is a very important basis to find the way to realize electronic devices based on this emergent material.

A new era of low-dimensional materials has indeed opened since a two-dimensional (2D) monolayer of layered graphite was successfully isolated by Geim and Novoselov through the mechanical exfoliation method in 2004 [114, 126, 127]. This first 2D monolayer graphitic system is widely known as graphene. Graphene is made of sp^2 hybridized carbon atoms packed in a highly symmetric hexagonal lattice [128]. The honeycomb network of graphene can be extended to create the basic building block of other carbon allotropes, in which it can be stacked to form 3D graphite [129], rolled to form (1D) nanotubes [130], cut to form 1D nanoribbons [131], and wrapped to form 0D fullerenes [132]. The orbital hybridization mechanism in graphene is that the C-($2s$, $2p_x$, and $2p_y$) orbitals are hybridized to create strong σ bonds to hold the planar 2D sheet, while C- $2p_z$ orbitals remain freestanding to form weak π bonding along the z -direction. This evidences that σ and π bonds in graphene are separated, in which the π orbitals mainly contribute to a Dirac cone structure at low-lying energy

[133]. Specifically, the long-range π conjugation in graphene leads to many novel quasiparticle properties that have been interested in many recent studies [134]. To date, graphene has been utilized in various applications such as flexible devices [135], transparent conductors [136], high-speed devices, and batteries [137]. Unfortunately, graphene displays many disadvantages for nanoelectronic applications due to its zero-gap feature [138]. To overcome the critical drawbacks of graphene, various approaches have been used to open a band gap in graphene, including chemical functionalizations [139], atom dopings [140], mechanical strains [141], bilayer structures [142], finite-size confinements [143], inducing defects [144], and applying external fields [145]. Beyond graphene, many efforts have been strongly focused on graphene-like 2D materials and other emergent 2D systems, including silicene [146], germanene [147], stanene [148], phosphorene [149], antimonene [150], bismuthene [151], transition metal dichalcogenides (TMDs) [152], topological insulators (TIs) [153], metal-organic frameworks (MOFs) [154], and Mxenes [155], in which silicene, a 2D analog of graphene, is made of silicon atoms packed in a low buckled honeycomb lattice. Silicene possesses many graphene-like quasiparticle features [156]; however, silicene presents better compatibility in silicon-based electronic devices than graphene so that silicene has stirred studies to extend its potential for practical applications [157]. Unlike graphene, silicene can only be synthesized through bottom-up methods due to a lack of graphite-like layered silicon structure. The most common method to synthesize the monolayer silicene is to deposit silicon atoms on the metallic substrates [158–160] that provide the experimental evidence for the presence of the 2D silicon sheet, which was theoretically predicted in 1994 [161]. Up to now, silicene has been extended in many applications, including room-temperature field-effect transistors (FETs) [162], gas sensors [163], and batteries [164]. Nevertheless, the critical disadvantage of silicene for electronic devices is its small gap feature [165]. Thus, a lot of studies have been conducted in opening band gap for silicene, including chemical modifications [166], quantum confinements [167], stacking configurations [43], mechanical strains [168], and applying external fields [169]. Among these methods, creating the finite size-quantum confinements is the most powerful way to create a band gap that can remain the low-buckled honeycomb lattice of 2D host silicene without any modification in the chemical hybridization mechanism in the honeycomb networks. The finite size confinements of 2D silicene result in 1D silicene nanoribbons (SiNRs) with armchair (ASiNR) and zigzag (ZSiNR) edges [170]. SiNRs show the middle-gap quasiparticle properties that can fully overcome the main obstacle of 2D host silicene for electronic devices [171]. On the experimental side, SiNRs have been successfully synthesized from both top-down and bottom-up methods. The top-down method is to cut the 2D host silicene to create 1D SiNRs [172], while the bottom-up approach is to grow 1D SiNRs on metallic substrates or an insulating thin film [173, 174]. SiNRs with their dominant quasiparticle features and their compatibility in silicon-based electronic devices have attracted much attention from the scientific community recently [175]. On the other hand, a wide range of applications requires materials having greater diverse quasiparticle properties such that enriching the essential quasiparticle properties of SiNRs is an interesting issue for many studies. To diversify the essential quasiparticle properties of SiNRs, various methods have been applied, including chemical dopings [176], edge passivations

[177], stacking configurations [178], generating lattice defects [179], applying external fields [180], and forming heterostructures [181], in which atom doping is the most effective way to dramatically diversify the essential quasiparticle properties. Up to now, many kinds of atoms have been successfully doped in SiNRs to result in their diversified quasiparticle properties [182–186]. However, halogen adsorptions on SiNRs have not yet been revealed in detail, while halogen adatoms with very strong electron affinity can create a strong bonding with silicon atoms to greatly complicate in chemical hybridization mechanism that can result in significant diversified quasiparticle properties. Therefore, the diverse quasiparticle properties of halogen-adsorbed SiNRs are worthy of further investigation in Chapter 5. Furthermore, the developed first-principles theoretical framework in this chapter can be fully generalized to many other emergent layered materials.

Graphene nanoribbon (GNR), a one-dimensional (1D) narrow strip of graphene [187–189], has recently attracted much attention due to its remarkable properties. 1D quantum confinement effects of a GNR can greatly diversify the essential properties, which can overcome the limitation of application in 2D graphene with its zero-gap electronic structure. Nanoribbon width and edge structure play critical roles in the essential properties of GNRs. According to the edge structure, there are two typical GNRs, armchair and zigzag ones (AGNRs and ZGNRs) [190, 191]. The former belongs to non-magnetic semiconductors, while the latter are anti-ferromagnetic middle-gap semiconductors. Up to now, GNRs have been successfully synthesized by various experimental methods such as lithographic [192, 193], sonochemical breaking [194], oxidization reaction [195], chemical vapor deposition [196], unzipping CNTs using plasma etching [197], and so on. Recently, GNRs are promising in the fields of energy storages, e.g., field-effect transistors [198], lithium-ion batteries [199, 200], and fuel cells [201]. To further expand the range of application, GNRs' properties can be modulated by changing the geometric structures [202, 203], doping [204, 205], and applying external electric/magnetic fields [206, 207]. Chapter 6 aims to provide a systematic study on the fundamental properties of the metal/transition metal adatom-adsorbed GNRs. The various Al-/Fe-/Co-/Ni-adsorption structures, critical multi-orbital hybridizations, significant non-magnetism (NM)/anti-ferromagnetism (AFM)/ferromagnetism (FM), and metallic/semiconducting behaviors will be clearly illustrated.

A single-wall carbon nanotube as well as silicon nanotube can be regarded as a rolled honeycomb lattice of graphene and silicene, respectively. The successful systematic studies of carbon nanotubes (CNTs) have been synthesized by means of arc-discharge evaporation in 1991 [208]. Later, other developments [209–213] such as characterization [214–217], property [218–220], and applications [221–223] sprang up like mushrooms. Similarly, silicon nanotubes (SiNTs) were successful initially synthesized in 2000 via ozone to remove the tubular meso- and nanoporous silicate templates [223]. Soon after that, a lot of investigations have been reported such as different growth process [224–226], features [226, 227], and applications [228–230]. The electronic properties of the planar graphene nanoribbons exhibit semiconducting behavior. On the other hand, the cylindrical carbon nanotubes are metals or direct-gap semiconductors sensitive to the chirality and radius. Metallic nanotubes are exclusively comprised of either armchair nanotubes or very small zigzag nanotubes

with radii $< \sqrt{3}b$ (b is the C-C bond length) [231]. The cylindrical silicon nanotubes exhibit the same behaviors as carbon nanotubes. They can be either metallic or semiconducting depending on the radii and chiral vectors. The Metallic silicon nanotubes are only comprised of zigzag types, especially for the small size of tubes ($(m,0)$, $m \leq 9$), and others are semiconducting such as armchair silicon nanotubes and large size of zigzag ones. Large curvature effect enhances the σ and π mixing in the smaller tubes, leading to the metallic property. The theoretical calculations [232, 233] and experimental measurement have confirmed the curvature effects, the misorientations of $2p_z$ orbitals and hybridizations of carbon ($2s$, $2p_x$, $2p_y$, $2p_z$) and silicon ($3s$, $3p_x$, $3p_y$, $3p_z$) four orbitals, on a cylindrical surface, leading to the geometry dependent energy gaps. Chapter 7 introduces single-wall carbon and silicon nanotubes with different diameters and chiralities. The geometric structure, energy bands, spatial charge distributions, and orbital-projected density of states are discussed in detail. Silicon nanotube is characterized by sp^3 hybridization and the gear-like structure. The ground state energy E_0 obviously decreases with the increasing diameter, owing to the reduction of bond length, buckling distance (for SiNTs), and curvature effect. The variation of the band structure and PDOSs with the curvature is investigated thoroughly. The calculated results clearly indicate the unusual features of the energy band, such as energy gap, energy dispersions, band-edge states, mixing bands, band overlap, and state degeneracy. The total and local DOSs exhibit a plenty of prominent asymmetric peaks in the inverse of the square-root form. The zigzag carbon and silicon nanotubes are quite different from each other, mainly owing to the curvature effect, unsymmetrical structure, and the open/periodical boundary condition. These could be directly verified by the STS measurements.

Chapter 8 offers an analysis of electronic, optical properties of pristine silicene and substituted-silicene by B, C, and N atoms using density functional theory. Such guest-atoms possess three, four, and five electrons in the outermost cell, being suitable for a deep understanding of the quasiparticle properties of the substitutional silicene systems. The optical coefficients such as the real and imaginary dielectric function, dielectric function, electron loss function, absorption coefficient, refractivity, and reflectivity are calculated for both in-plane light polarization (perpendicular) and out of plane (parallel) polarization. The electronic and optical properties of the guest-substituted silicene systems become so different compare with the pristine ones. Our computational results present the p-type doping metallic behavior in boron-substituted silicene while in the carbon- and nitrogen-substituted cases, the systems become semiconducting phenomena. The absorption intensity in the case of carbon-substituted silicene is highest in both polarization directions, but in the case of boron and nitrogen, it is almost unchanged compared to pristine. The comparison between the guest-atoms substitution and the pristine systems will be discussed in detail in all the properties.

Binary compounds, fully B-/C-/N-substituted germanenes, exhibit the diversified phenomena through the different chemical bondings presented in Chapter 9. The delicate first-principles calculations can present the buckling/planar honeycomb lattices, the atom-dominated band structures, the spatial charge densities, the spin density distributions, and the atom-, orbital-, and spin-decomposed density of states, being very useful in determining the critical orbital hybridizations and magnetic

configurations. The concise pictures, the strong competition between sp^2 and sp^3 bondings, and the guest-dependent spin states, are responsible for the geometric symmetries, the metallic/wide-/narrow-gap behaviors, the modification/destruction of Dirac-cone structures, the nonmagnetic or ferromagnetic properties, the crossings/anti-crossings of π and σ bands, or the pure sp^3 energy bands.

Plumbene, the latest cousin of graphene, has been mentioned as a candidate material for topological insulator (TI) and room-temperature operations [12, 234] due to its rich and unique geometric and electronic properties. In 2019, Yuhara and his coworkers reported the successful fabrication of the single layer of lead atoms by molecular beam epitaxy (MBE) [235]. This work has prompted the development of related research, e.g., chemical decoration and/or hydrogenate of monolayer Plumbene. The chemical modifications, as revealed in the experimental and theoretical investigations [236, 237], are one of the most efficient approaches in dramatically changing the geometric, electronic, and optical properties through orbital hybridization modification. Very interestingly, the Hydrogen atom with $1s$ orbital in the electronic configuration exhibits the extremely strong chemical bonding with the Pb atom in Plumbene. The critical quasiparticle features include the significant orbital hybridizations in Pb-H chemical bonds, the significant change of the electronic properties in double and single side adsorption, the modify of optical spectrum in case of with/without excitonic effect, and very importantly, the effect of spin-orbital couplings on the electronic and optical properties of the hydrogenated systems are thoroughly examined from the first-principles simulations in Chapter 10. The current study is very useful in comprehending the crucial properties of 2D materials with chemical functionality.

Graphite is one of the mainstream materials in basic science research and potential applications [238]. Apparently, this system stirred plenty of theoretical and experimental [239, 240] studies more than one hundred years ago. Its layered structure, which consists of carbon mb lattices, exhibits the unusual crystal symmetries [241] and thus the unusual phenomena, such as, the AA [242], AB [242], ABC [243], and turbostratic stackings [244]. The graphitic spacing, being determined by the Van der Waals interactions [245], provides a very active environment in creating the chemical intercalations or de-intercalations for the various atoms/molecules/ions [246], especially for the charging and discharging processes in ion-based batteries [247]. The chemical modifications are capable of generating the n -, p -type dopings [248] or even the zero-gap semiconducting behaviors [249], the drastic changes of band structures and van Hove singularities through the zone-folding effects and significant intercalant-related interactions [13], the featured optical reflectance and absorption spectra in the presence/absence of quasi-stable excitons [250], the diverse (momentum, frequency)-dependent Coulomb excitations under distinct free carriers (the rich electron-hole and collective excitations), the very high electrical conductivities comparable to those metals, and a great enhancement of the superconducting transition temperature [250]. Very interestingly, this rather stable system is frequently utilized as the anode/cathode materials of lithium/aluminum-based batteries. The rich essential properties have been studied for the Li- and Li^+ -related graphite intercalation compounds [249]. The critical quasiparticle properties, the significant orbital hybridizations in various intralayer and interlayer chemical bonds, are thoroughly

examined from the first-principles simulations in Chapter 11. The intercalations and de-intercalations of large molecules are expected to become more complicated, mainly owing to the enlarged Moiré superlattices [251]. This study is very useful in comprehending aluminum-based batteries [252], certain important differences among the different graphite intercalation compounds, and close relations between the numerical methods and the phenomenological models [253].

Batteries [254], which store and release energy in terms of chemical energy, have become one of the mainstream items in research recently. Compared with other energy store systems, lithium-ion-based batteries (LIBs) have received a great deal of attention since they process desirable features, such as light weight, long life cycle, fast charging time, and ability to provide a sizable electronic current for electronic devices [255, 256]. Generally speaking, the commercial LIB is a complex combination of the electrolyte with the negative (cathode) and the positive (anode) electrodes [255, 256]. Furthermore, the physical/chemical pictures in each component are rather complicated and directly related to the performance of storage systems. The previous few theoretical studies are conducted on the geometric and electronic properties of LIBs' components through the first-principles calculations. However, the delicate results and analyses have been thoroughly absent up to now. That is to say, the calculated results are insufficient, and there are no critical mechanisms (concise physical pictures) in comprehending the diversified phenomena. The theoretical framework is based on the numerical calculations and delicate analyses were developed and applied for the layered LiFeO_2 -a candidate for cathode compound in Chapter 12. The fundamental features, the critical quasiparticle properties, and the significant orbital hybridizations in various chemical bonds are thoroughly examined from the first-principles simulations. The charging and discharging of LIBs are expected to be complicated owing to the variation of chemical bonds and thus, orbital hybridizations. Our predictions provide certain meaningful information about the critical physical/chemical pictures in LIBs. Such state-of-the-art analysis is very useful for fully comprehending the diversified properties in anode/cathode/electrolyte and other emerging materials.

Beyond graphene, atomically thin TMDs have become a new platform owing to their rich and unique properties [257–260]. Especially, the change in properties from monolayer to bilayer is more significant than that resulting from multilayers [261–264]. Bilayer TMDs reveal the interesting and unique properties compared to their monolayers such as higher density of states and carrier mobility [265–268]. This phenomenon anticipates superior performance in thin-film transistors and sensors. In addition, stacking orders in bilayer exhibit an alternative method in investigating their effects. Varying stacking modes in structural engineering can manipulate the electronic properties of bilayer TMDs as reported in MoS_2 [269–271] and WS_2 [272]. Among TMDs, HfX_2 ($X = \text{S}, \text{Se}, \text{or Te}$) is a group candidate that promises opportunities for investigation and applications based on their emergent and satisfactory findings. In the attempt to vary layered materials for reduction in the size of devices, layered structures such as monolayer or bilayer have been concerned. Besides, bulk and monolayer of HfX_2 had been explored and used in some electronic devices [273–276]. Bilayer HfX_2 should be therefore analyzed in order to enhance this group. Although bilayer HfSe_2 [277] has been studied and found promising for

thermal conductivity, the perspective of all these materials in bilayer is still limited. Using VASP calculations, the quasiparticle problems related to electrons as formerly mentioned are resolved, indicating the close relations between theoretical framework and quasiparticles. In Chapter 13, we focus on the electronic properties of these materials constructed in bilayer to provide further information about their features.

Lithium-ion batteries have become popular and dominate in commercial purposes. They possess many high-performance characteristics such as high power, energy density, long life cycle, and friendly to the environment, as well as affordable prices. Many candidates are investigated further as potential cathode, anode, and electrolyte components. Our study in this chapter focuses on an excellent anode material with the zero-strain property of the volume during the lithium intercalation or deintercalation process. The ternary compound possesses a lot of advantages, e.g., the safety and long cycling life for lithium-ion batteries. Currently, $\text{Li}_4\text{Ti}_5\text{O}_{12}$ enters into the commercial anode product for Li^+ -ion based batteries [278, 279]. Lithium titanate material presents rich and unique geometric, electronic properties under the quasiparticle framework [39, 278, 279]. The primitive cell contains a huge number of atoms, which is called a Moiré superlattice [39]. The geometric structure performs a non-uniform environment, which fundamentally comes from the Li-O and Ti-O bonds. Many significant electronic quasiparticle properties are presented such as band structures, atom-dominated energy spectrum, spatial charge density distributions, and the atom- or the orbital-decomposed density of states [279]. The theoretical quasiparticle properties could be tested under the high-resolution experimental measurements. Many experimental examinations can be used for investigating the whole structures, e.g., X-ray diffractions for measuring the lattice parameters, transmission electron microscopy (TEM) for morphology [280], angle-resolved photo-emission spectroscopy (ARPES [281–283]), and scanning tunneling spectroscopy (STS [283–285]) for band structures examination along with van Hove singularities. Also, the theoretical development of a quasiparticle framework in geometry and the electronic in terms of multi-hybridizations is worthy to thoroughly investigate in Chapter 14.

In Chapter 15, the theoretical calculations for the low-lying vibrational H atoms adsorbed on the Pt(110) surface are presented. We use the H/Pt(110) model with the conventional ultrahigh vacuum (UHV) and the density functional theory (DFT) to study the phonon frequency (the quasiparticle frequency). The nature of hydrogen atoms, which were adsorbed on the four different sites of the Pt(110) surface, is shown. The most stable site of the short bridge is in agreement with previous studies. The highest stretching frequency of 2200 cm^{-1} and the zero-point energy (ZPE) of the H atom on the top site $\sim 140\text{ meV}$ are calculated. Our results convincingly demonstrate the need to study the local oscillation to understand the dynamics of this system.

Bismuth chalcogenides are of great interest because of the exciting properties of topological insulators (TIs) and their potential applications in low power dissipation electronic devices, spintronics, and quantum computing. TIs are exotic materials with an insulating bulk and topologically protected surface states (TSSs) that exhibits Dirac linear energy dispersion inside the bulk gap, spin-polarization by spin-momentum locking nature. In bismuth chalcogenide TIs (e.g., Bi_2Te_3 , Bi_2Se_3 ,

$\text{Bi}_2\text{Se}_2\text{Te}$, etc.), the dominant bulk conduction arising from naturally occurring crystal imperfections and residual carrier doping has greatly hindered the detection of Dirac fermions by means of weak anti-localization effect (WAL) and quantum oscillations at low temperatures. Regardless of such challenges, the transport method has been great success in probing the TSSs and studying its properties. The WAL effect agrees well with the Hikami-Larkin-Nagaoka model that allows to obtain the number of conduction channel and phase coherent length. However, in TIs, since the WAL reflects both the 3D contribution of spin-orbit coupling in bulk and the Dirac nature of the 2D TSSs, a detailed study of magnetoconductance ($\Delta G(\theta, B)$) in tilted magnetic fields ($\theta = 0-90^\circ$) is essential to get insight into the origin of the observed WAL. If all the ΔG curves coincide with each other in the plot of $\Delta G(\theta, B)$ versus the perpendicular component of the magnetic field, then the observed WAL effect is 2D in nature. In addition, TIs with sufficiently high surface electron mobility can present pronounced Shubnikov-de Haas (SdH) oscillations. The analysis of SdH oscillations leads to elucidating the Dirac nature of TSS with finite Berry phase and 2D Fermi surface; it also enables us to extract the carrier concentration, effective mass, Dingle temperature, and the Berry phase of TIs. Chapter 16 presents the recent advances in magnetotransport method to study on bismuth chalcogenide TIs and their most fascinating results.

Current emerging materials provide us with various significant applications in industry, particularly in energy storage and electronic equipment. In battery applications, LiFeO_2 can be served as a cathode material, while silicon-carbon nanotubes and $\text{Li}_4\text{Ti}_5\text{O}_{12}$ are popular for the anode side. Aluminum-chloride-graphene intercalated compounds are known as an abundant and friendly environment, which can contribute to the development of ion-based batteries. Other materials have significant applications in electronic and photoelectronic devices such as transition metal dichalcogenides (TMDs) material group HfX_2 ($X = \text{S}, \text{Se}, \text{or Te}$), Bismuth chalcogenide topological insulators (BiCh-TIs). In addition, penta-graphene nanoribbons metals/transition metals and halogen-adsorbed silicene nanoribbons can be developed for certain heterojunction devices and spintronics, respectively. Remarkably, spintronics is used to monitor the spin properties, which are based on the natural characteristics of electrons. Furthermore, hydrogenated absorption systems, for example, the adsorbed hydrogen on the Pt(110) surface, plumbene adsorption hydrogen, and hydrogen adsorption on two-dimensional germanene are developed to enhance hydrogen technology and battery applications. substituted silicene systems germanene and silicene systems can be useful for light and lasers due to their wide band gap. Chapter 17 will present diverse practical contributions of these materials in industrial and daily applications.

In summary, Chapter 2 covers the theoretical frameworks of quasiparticle particles from both viewpoints of first-principles simulations and phenomenological models [286], as generalized from the precious developments [287]. The high-resolution experimental measurements are thoroughly characterized in Chapter 3. By delicate VASP calculations and analyses, the diverse quasiparticle phenomena clearly reveal in penta-graphene nanographene nanoribbons [Chapter 4], halogenated silicene nanoribbons [Chapter 5], metals/transition metals-adsorbed graphene nanoribbons [Chapter 6], zigzag silicon nanotubes [Chapter 7], boron-/carbon-/

nitrogen-substituted silicene [Chapter 8], adatom-substituted on germanene systems [Chapter 9], hydrogen-chemisorption plumbenes [Chapter 10], stage-1/stage-2/stage-3/stage-4 AlCl_4 graphite intercalation compounds [Chapter 11], ternary lithium iron oxides [Chapter 12], different stacking in bilayer HfX_2 ($\text{X}=\text{S}$, Se , or Te) [Chapter 13], lithium titanium oxides [Chapter 14], H-adsorbed $\text{Pt}(110)$ surfaces [Chapter 15], and bismuth Chalcogenide topological Insulators [Chapter 16]. In addition to the theoretical analysis, the diverse related practical applications of these emerging materials will be covered in this book [Chapter 17].

In concluding remarks, the calculated results include the total ground state energies/the chemical modification energies [288], the optimal Moiré superlattices/normal unit cells [289], the atom- and spin-dominated band structures/wave functions [25], the spatial charge/spin density distributions [36], the atom- orbital- and spin-decomposed van Hove singularities [37], the net magnetic moments [205], the single-particle and many-body reflectance [290], absorption [291], transmission [292] and energy loss spectra [293], the ballistic electrical conductivities [294], the Hall quantum ones [295], and the vibration phonons [296]. They are very sufficient in identifying the various quasiparticle behaviors and further generalize the previous theoretical framework [297]. Concluding remarks, open issues, and obvious problems are, respectively, illustrated in Chapter 18–20.

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